Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	60	V
Gate-Source Voltage			V_{GSS}	±20	V
Continuous Drain Current (Note 6) V_{GS} = 10V	Steady State	T_A = +25°C T_A = +70°C	I_D	4.1 3.3	A
Pulsed Drain Current (10µs Pulse, Duty Cycle ≦1%)			I_{DM}	15	A
Maximum Body Diode Continuous Current (Note 6)			I_S	2.5	A
Pulsed Body Diode Current (10µs Pulse, Duty Cycle ≦1%)			I_{SM}	15	A
Avalanche Current, L=0.1mH (Note 7)			I_{AS}	11	A
Avalanche Energy, L=0.1mH (Note 7)			E_{AS}	6	mJ

Thermal Characteristics

Characteristic		Symbol	Value	Unit
Total Power Dissipation (Note 5)	T_A = +25°C	P_D	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	122	°C/W
	t<10s		72	°C/W
Total Power Dissipation (Note 6)	T_A = +25°C	P_D	2.1	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{\theta JA}$	58	°C/W
	t<10s		34	°C/W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	12	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	60	—	—	V	I_D = 250µA, V_{GS}= 0V
Zero Gate Voltage Drain Current	I_{DSS}	—	—	1	µA	V_{DS}= 60V, V_{GS}= 0V
Gate-Source Leakage	I_{GSS}	—	—	±100	nA	V_{GS}= ±16V, V_{DS}= 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	1.0	—	3.0	V	I_D= 250µA, V_{DS}= V_{GS}
Static Drain-Source On-Resistance	$R_{DS(ON)}$	—	70	85	mΩ	V_{GS}= 10V, I_D= 2.5A
			76	110		V_{GS}= 4.5V, I_D= 1.5A
Diode Forward Voltage	V_{SD}	—	0.75	1.2	V	I_S= 12A, V_{GS}= 0V
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{iss}	—	588	—	pF	V_{DS}= 30V, V_{GS}= 0V f= 1MHz
Output Capacitance	C_{oss}	—	26.5	—		
Reverse Transfer Capacitance	C_{rss}	—	20	—		
Gate Resistance	R_g	—	1.5	—	Ω	Vgs= 0V, Vds= 0V, f=1MHz,
Total Gate Charge (V_{GS}= 4.5V)	Q_g	—	5.6	—	nC	V_{DS}= 30V, I_D= 3A
Total Gate Charge (V_{GS}= 10V)	Q_g	—	12.3	—		
Gate-Source Charge	Q_{gs}	—	1.7	—		
Gate-Drain Charge	Q_{gd}	—	1.9	—		
Turn-On Delay Time	$t_{D(ON)}$	—	3.5	—	ns	V_{DD}= 30V, V_{GS}= 10V R_L ≅ 50Ω, R_g ≅ 20Ω
Turn-On Rise Time	t_R	—	4.1	—		
Turn-Off Delay Time	$t_{D(OFF)}$	—	35	—		
Turn-Off Fall Time	t_F	—	11	—		
Body Diode Reverse Recovery Time	t_{RR}	—	18	—	ns	I_S = 12A, di/dt = 100A/µs
Body Diode Reverse Recovery Charge	Q_{RR}	—	12	—	nC	I_S = 12A, di/dt = 100A/µs

Notes:
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided.
6. Device mounted on FR-4 substrate PC board, 2oz copper, with thermal bias to bottom layer 1inch square copper plate.
7. I_{AS} and E_{AS} ratings are based on low frequency and duty cycles to keep T_J = +25°C.
8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

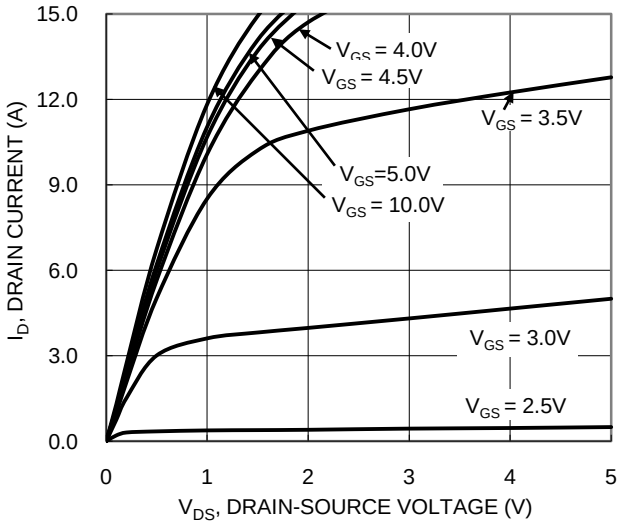

Figure 1. Typical Output Characteristic

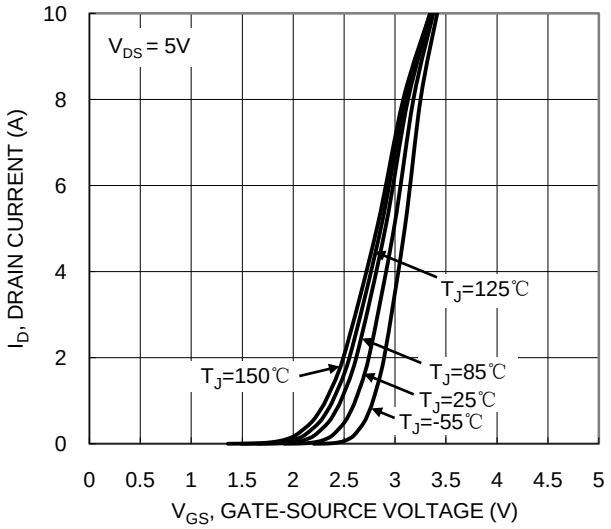

Figure 2. Typical Transfer Characteristic

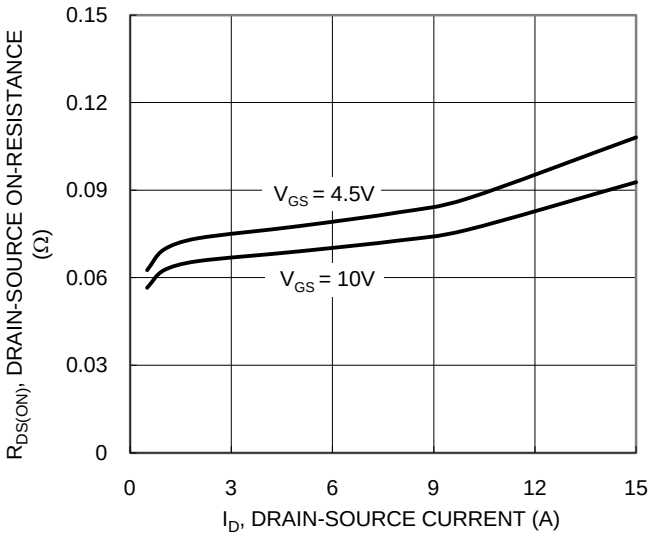

Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

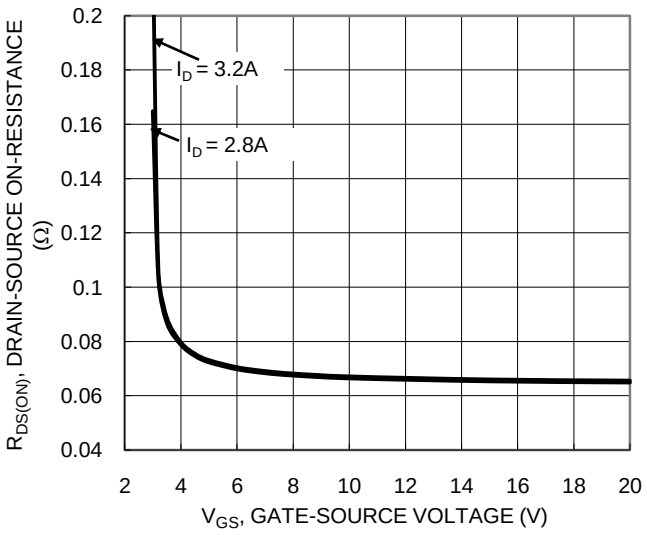

Figure 4. Typical Transfer Characteristic

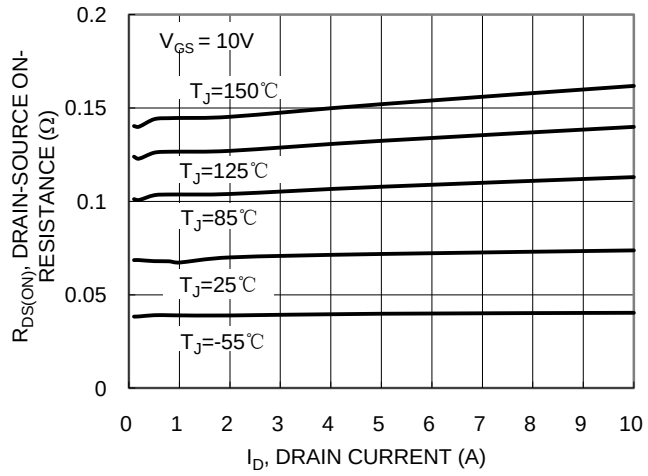

Figure 5.Typical On-Resistance vs. Drain Current and Temperature

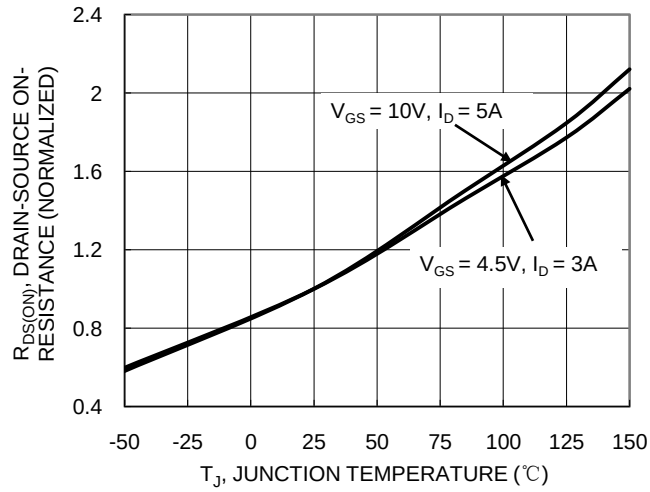

Figure 6. On-Resistance Variation with Temperature

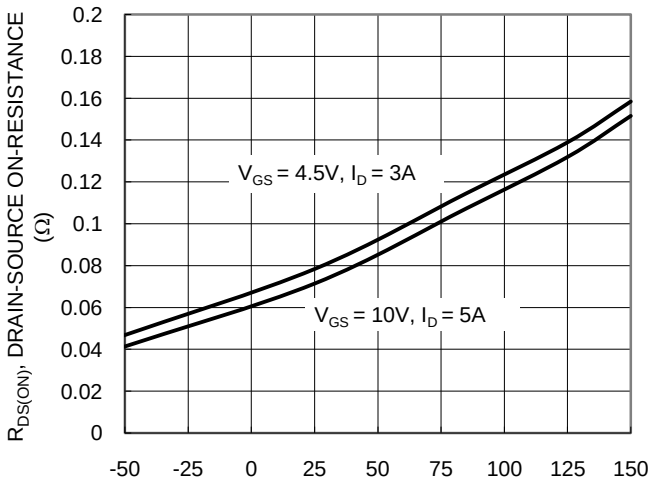

Figure 7. On-Resistance Variation with Temperature

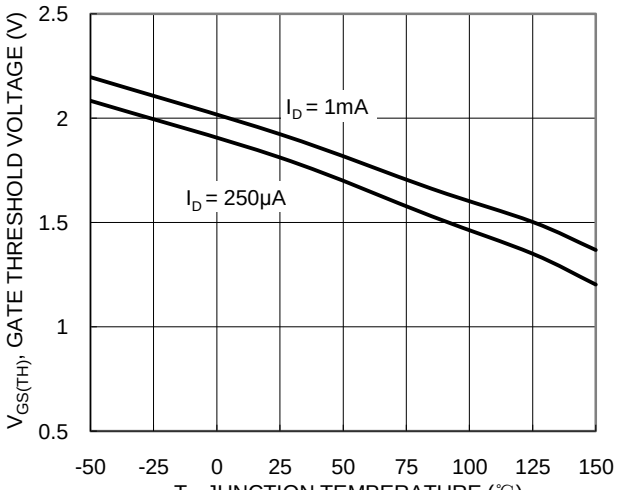

Figure 8. Gate Threshold Variation vs. Junction Temperature

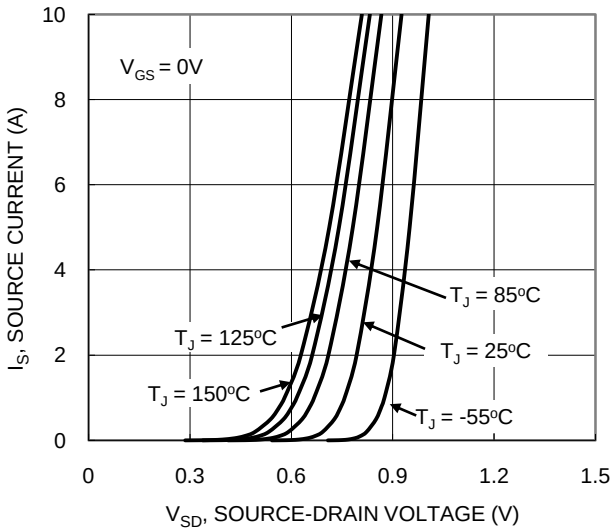

Figure 9. Diode Forward Voltage vs. Current

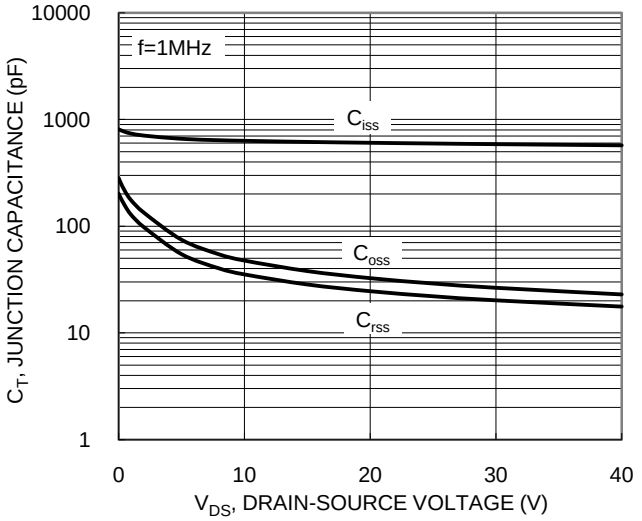

Figure 10. Typical Junction Capacitance

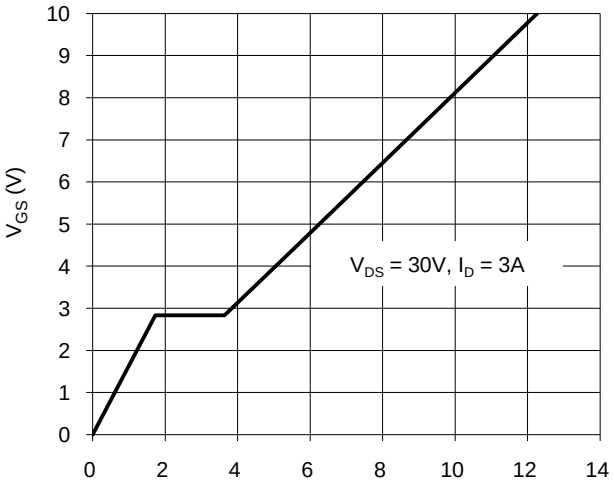

Figure 11. Gate Charge

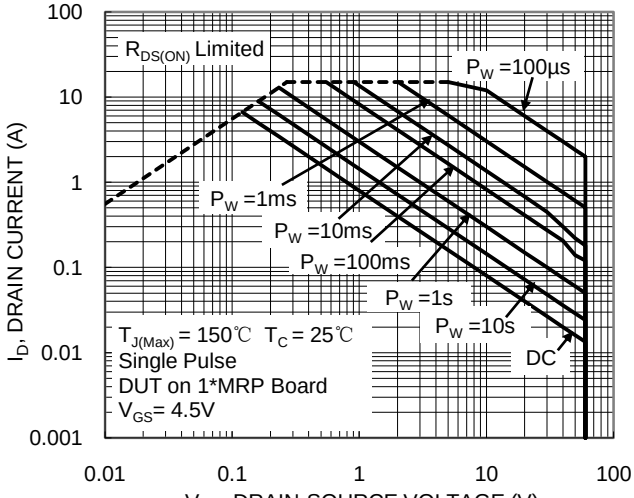

Figure 12. SOA, Safe Operation Area

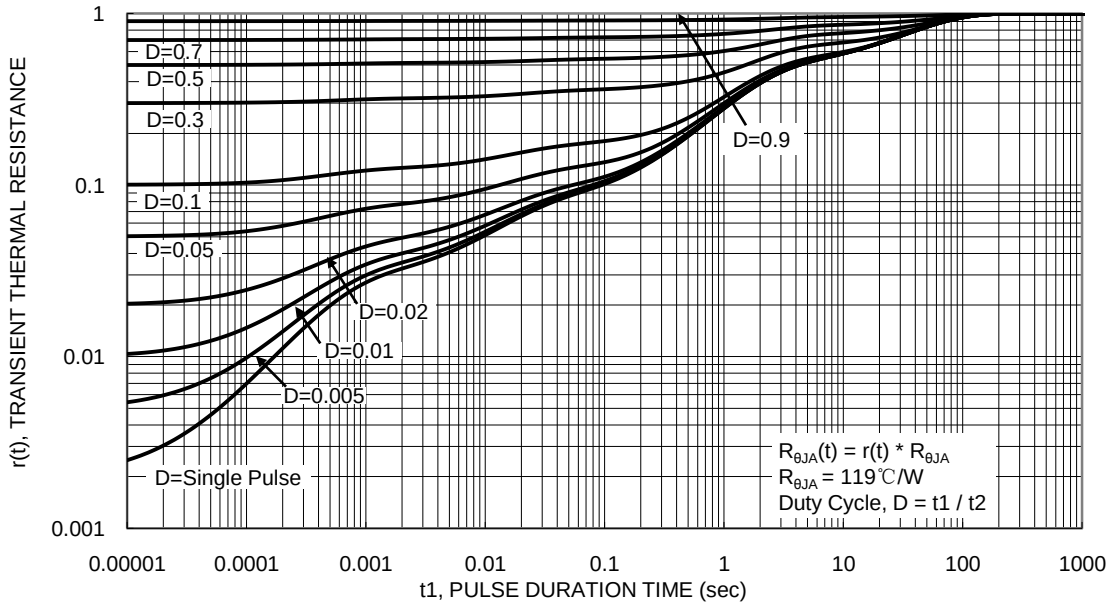

Figure 13. Transient Thermal Resistance

Package Outline Dimensions

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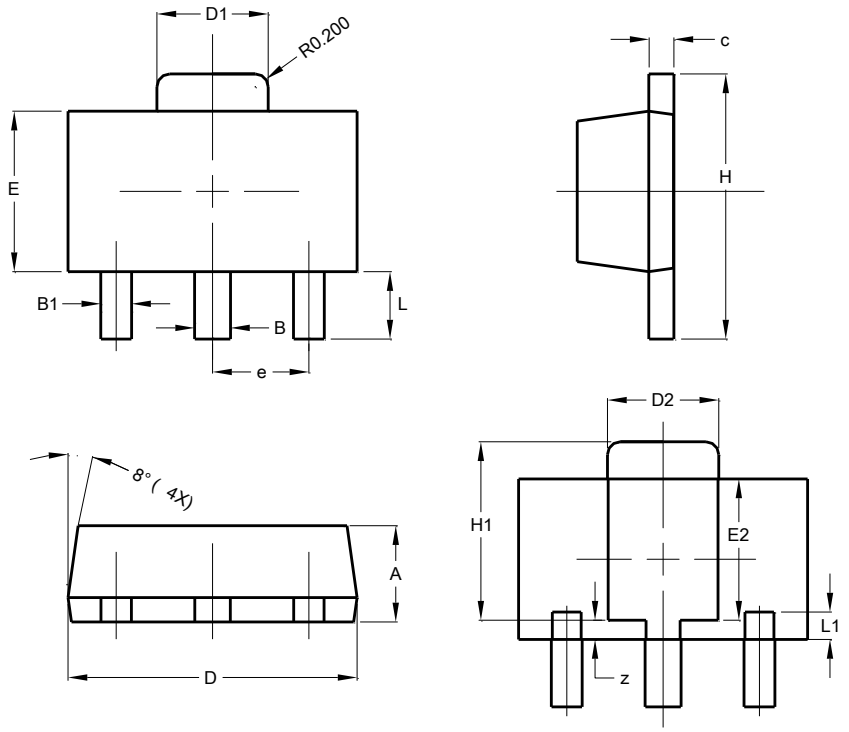
SOT89

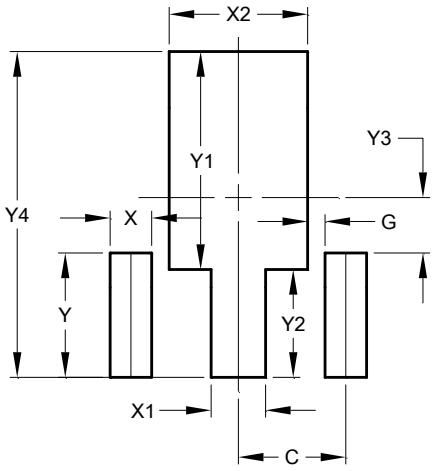


SOT89			
Dim	**Min**	**Max**	**Typ**
A	1.40	1.60	1.50
B	0.50	0.62	0.56
B1	0.42	0.54	0.48
c	0.35	0.43	0.38
D	4.40	4.60	4.50
D1	1.62	1.83	1.733
D2	1.61	1.81	1.71
E	2.40	2.60	2.50
E2	2.05	2.35	2.20
e	-	-	1.50
H	3.95	4.25	4.10
H1	2.63	2.93	2.78
L	0.90	1.20	1.05
L1	0.327	0.527	0.427
z	0.20	0.40	0.30
All Dimensions in mm			

Suggested Pad Layout

Please see http://www.diodes.com/package-outlines.html for the latest version.

SOT89



Dimensions	Value (in mm)
C	1.500
G	0.244
X	0.580
X1	0.760
X2	1.933
Y	1.730
Y1	3.030
Y2	1.500
Y3	0.770
Y4	4.530

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